## **N-Channel Switch**

# J111, J112, J113, MMBFJ111, MMBFJ112, MMBFJ113

#### **Features**

- This Device is Designed for Low Level Analog Switching, Sample and Hold Circuits and Chopper Stabilized Amplifiers
- Sourced from Process 51
- Source & Drain are Interchangeable
- These are Pb-Free Devices

# **ABSOLUTE MAXIMUM RATINGS** ( $T_A = 25$ °C unless otherwise noted) (Note 1, 2)

Symbol	Parameter	Value	Unit
$V_{DG}$	Drain-Gate Voltage	35	V
V <sub>GS</sub>	Gate-Source Voltage	-35	V
I <sub>GF</sub>	Forward Gate Current	50	mA
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	–55 to 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. These ratings are based on a maximum junction temperature of 150°C.
- These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed or low-duty-cycle operations.

#### THERMAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

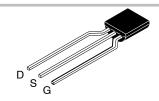
		Ma	ax	
Symbol	Parameter	J111 / J112 / J113 (Note 3)	MMBFJ111 / MMBFJ112 / MMBFJ113 (Note 4)	Unit
$P_{D}$	Total Device Dissipation	625	350	mW
	Derate Above 25°C	5.0	2.8	mW/°C
$R_{ heta JC}$	Thermal Resistance, Junction-to-Case	125	-	°C/W
$R_{ heta JA}$	Thermal Resistance, Junction-to-Ambient	200	357	°C/W

- 3. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.
- Device mounted on FR-4 PCB 36 mm x 18 mm x 1.5 mm; mounting pad for the collector lead minimum 6 cm<sup>2</sup>.

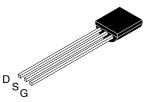


#### ON Semiconductor®

#### www.onsemi.com



TO-92 3 4.83x4.76 LEADFORMED CASE 135AR



TO-92 3 4.825x4.76 CASE 135AN

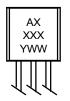


SOT-23 (TO-236) CASE 318-08



SOT-23 CASE 318BM

#### **MARKING DIAGRAMS**





XXXX, XX = Specific Device Code A = Assembly Plant Code

Y = Year WW = Work Week M = Date Code

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 6 of this data sheet.

#### **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ unless otherwise noted)

		<u> </u>				
Symbol	Parameter	Test Conditi	on	Min	Max	Unit
OFF CHARA	ACTERISTICS					
V <sub>(BR)GSS</sub>	Gate-Source Breakdown Voltage	$I_G = -1.0 \mu\text{A},  V_{DS} = 0$		-35	-	V
I <sub>GSS</sub>	Gate Reverse Current	$V_{GS} = -15 \text{ V}, V_{DS} = 0$		-	-1.0	nA
V <sub>GS</sub> (off)	Gate-Source Cut-Off Voltage	$V_{DS} = 5 \text{ V}, I_{D} = 1.0 \mu\text{A}$	111	-3.0	-10.0	V
			112	-1.0	-5.0	
			113	-0.5	-3.0	
I <sub>D</sub> (off)	Drain Cutoff Leakage Current	$V_{DS} = 5.0 \text{ V}, V_{GS} = -10 \text{ V}$	V	-	1.0	nA
ON CHARA	CTERISTICS					
I <sub>DSS</sub>	Zero-Gate Voltage Drain Current (Note 5)	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0	111	20	-	mA
			112	5.0	_	
			113	2.0	_	1
r <sub>DS</sub> (on)	Drain-Source On Resistance	$V_{DS} \le 0.1 \text{ V, } V_{GS} = 0$	111	-	30	Ω
			112	-	50	1
			113	-	100	1
MALL SIG	NAL CHARACTERISTICS		•			
$C_{dg}(on)$ $C_{sg}(on)$	Drain-Gate &Source-Gate On Capacitance	$V_{DS} = 0$ , $V_{GS} = 0$ , $f = 1.0$	) MHz	-	28	pF
C <sub>dg</sub> (off)	Drain-Gate Off Capacitance	V <sub>DS</sub> = 0, V <sub>GS</sub> = -10 V, f	= 1.0 MHz	-	5.0	pF
C <sub>sg</sub> (off)	Source-Gate Off Capacitance	V <sub>DS</sub> = 0, V <sub>GS</sub> = -10 V, f =	= 1.0 MHz	-	5.0	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse test: pulse width ≤300 μs, duty cycle ≤2%.

#### TYPICAL PERFORMANCE CHARACTERISTICS

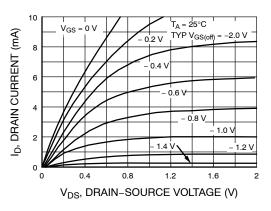
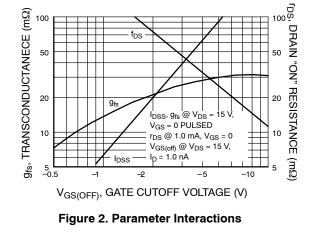
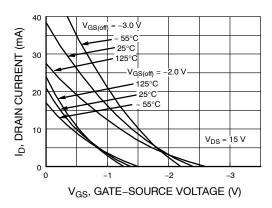
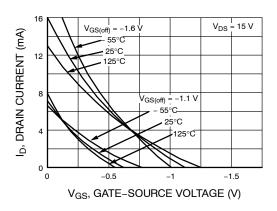


Figure 1. Common Drain-Source





**Figure 3. Transfer Characteristics** 



**Figure 4. Transfer Characteristics** 

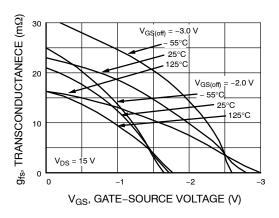


Figure 5. Transfer Characteristics

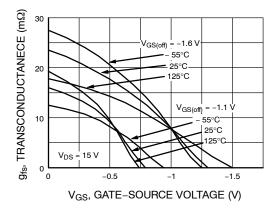


Figure 6. Transfer Characteristics

#### TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

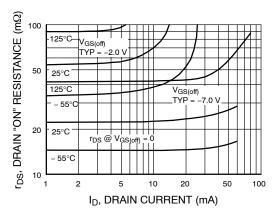


Figure 7. On Resistance vs. Drain Current

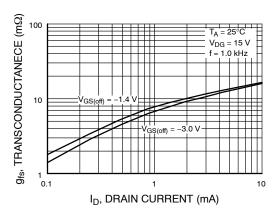


Figure 9. Transconductance vs. Drain Current

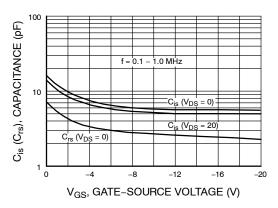


Figure 11. Capacitance vs. Voltage

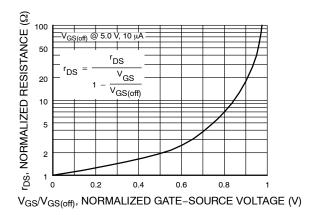


Figure 8. Normalized Drain Resistance vs. Bias Voltage

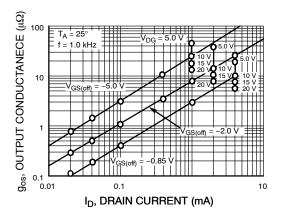


Figure 10. Output Conductance vs. Drain Current

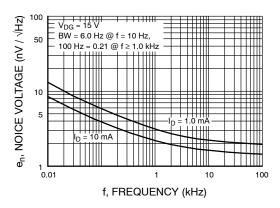


Figure 12. Noise Voltage vs. Frequency

#### TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

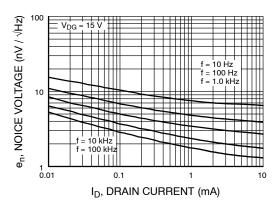


Figure 13. Noise Voltage vs. Current

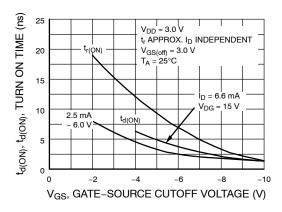


Figure 15. Switching Turn-On Time vs.
Gate-Source Voltage

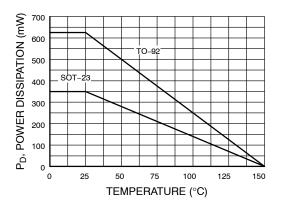


Figure 14. Power Dissipation vs.
Ambient Temperature

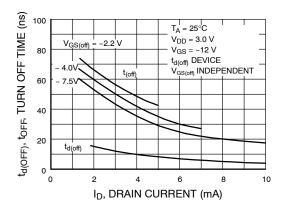


Figure 16. Switching Turn-Off Time vs.
Drain Current

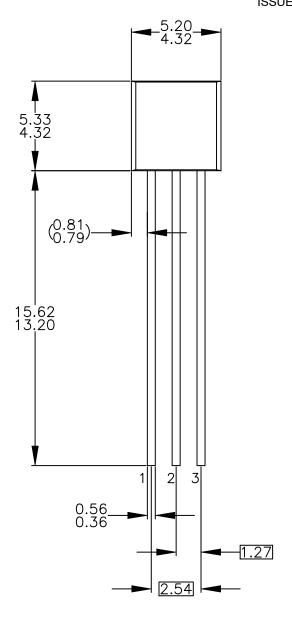
#### **ORDERING INFORMATION**

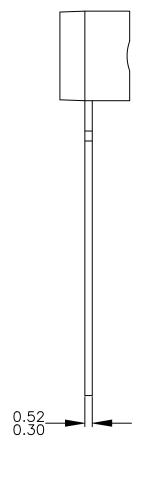
Part Number	Top Mark	Package	Shipping <sup>†</sup>
J111	AJ 111 YWW	TO-92 3L (Pb-Free)	10000 Units / Bulk
J111-D26Z	AJ 111 YWW	TO-92 3L (Pb-Free)	2000 / Tape & Reel
J111-D74Z	AJ 111 YWW	TO-92 3L (Pb-Free)	2000 / Ammo
J112	AJ 112 YWW	TO-92 3L (Pb-Free)	10000 Units / Bulk
J112-D26Z	AJ 112 YWW	TO-92 3L (Pb-Free)	2000 / Tape & Reel
J112-D27Z	AJ 112 YWW	TO-92 3L (Pb-Free)	2000 / Tape & Reel
J112-D74Z	AJ 112 YWW	TO-92 3L (Pb-Free)	2000 / Ammo
J113	AJ 113 YWW	TO-92 3L (Pb-Free)	10000 Units / Bulk
J113-D74Z	AJ 113 YWW	TO-92 3L (Pb-Free)	2000 / Ammo
MMBFJ111	6P	SOT-23 3L (Pb-Free)	3000 / Tape & Reel
MMBFJ112	6R	SOT-23 3L (Pb-Free)	3000 / Tape & Reel
MMBFJ113	6S	SOT-23 3L (Pb-Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### TO-92 3 4.825x4.76 CASE 135AN ISSUE O

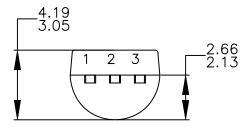
**DATE 31 JUL 2016** 





NOTES: UNLESS OTHERWISE SPECIFIED

- DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS. A)
- ALL DIMENSIONS ARE IN MILLIMETERS.
  DRAWING CONFORMS TO ASME Y14.5M—2009.



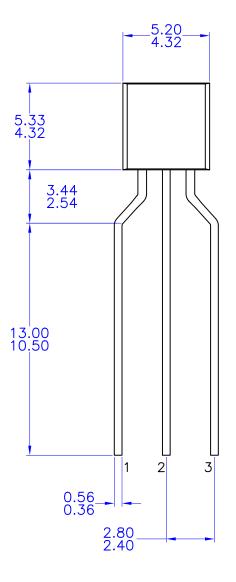
DOCUMENT NUMBER:	98AON13880G	Electronic versions are uncontrolled except when accessed directly from the Document Repository Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	TO-92 3 4.825X4.76	•	PAGE 1 OF 1	

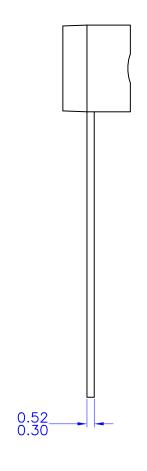
ON Semiconductor and at a trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

#### TO-92 3 4.83x4.76 LEADFORMED

CASE 135AR ISSUE O

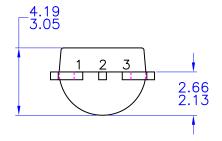
**DATE 30 SEP 2016** 





NOTES: UNLESS OTHERWISE SPECIFIED

- A) DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DRAWING CONFORMS TO ASME Y14.5M-1994



DOCUMENT NUMBER:	MBER: 98AON13879G Electronic versions are uncontrolled except when accessed directly from the Document Reprinted versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	TO-92 3 4.83X4.76 LEADFORMED		PAGE 1 OF 1

ON Semiconductor and at a trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

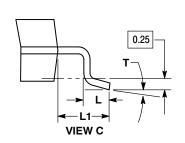


SOT-23 (TO-236) CASE 318-08 **ISSUE AS** 

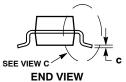
**DATE 30 JAN 2018** 

# SCALE 4:1 D - 3X b

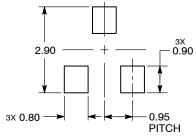
**TOP VIEW** 







#### **RECOMMENDED SOLDERING FOOTPRINT**



DIMENSIONS: MILLIMETERS

3. ANODE

#### NOTES:

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	O٥		100	O٥		10°

#### **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

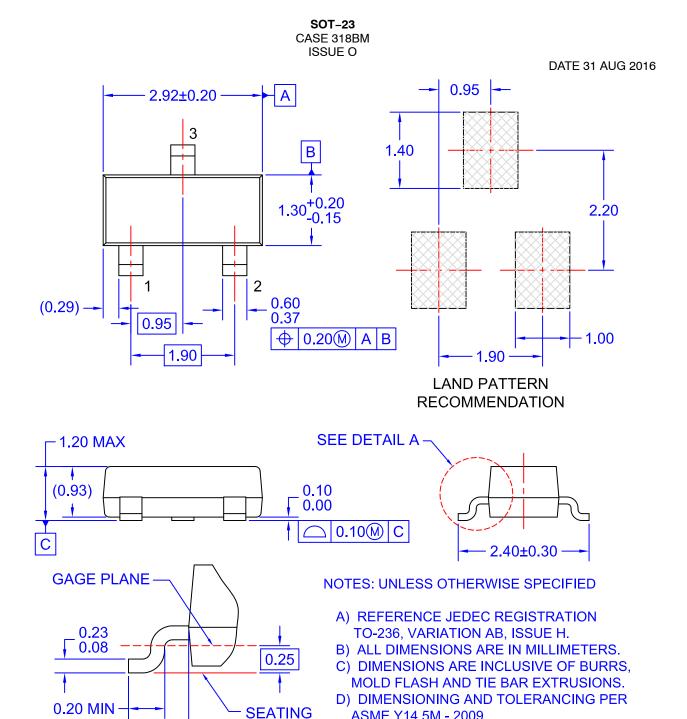
STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE				

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Reposit Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOT-23 (TO-236)		PAGE 1 OF 1

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

3. CATHODE





DETAIL A	
SCALE: 2X	

(0.55)

DOCUMENT NUMBER:	98AON13784G	Electronic versions are uncontrolled except when accessed directly from the Document Repo Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOT-23	•	PAGE 1 OF 1

**PLANE** 

ASME Y14.5M - 2009.

ON Semiconductor and un are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

ON Semiconductor and the are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and

#### **PUBLICATION ORDERING INFORMATION**

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative